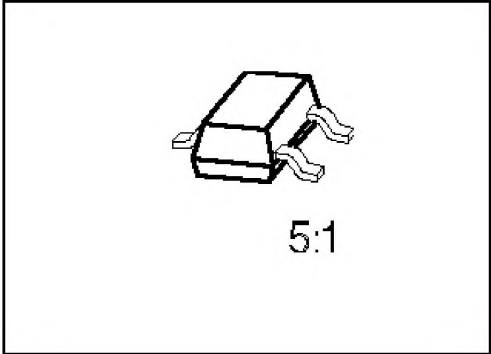


NPN Silicon High-Voltage Transistors

BFN 24
BFN 26

- Suitable for video output stages in TV sets and switching power supplies
- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary types: BFN 25, BFN 27 (PNP)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration			Package ¹⁾
			1	2	3	
BFN 24 BFN 26	FHs FJs	Q62702-F1065 Q62702-F976	B	E	C	SOT-23

Maximum Ratings

Parameter	Symbol	Values		Unit
		BFN 24	BFN 26	
Collector-emitter voltage	V_{CE0}	250	300	V
Collector-base voltage	V_{CB0}	250	300	
Emitter-base voltage	V_{EB0}	5		
Collector current	I_C	200		mA
Peak collector current	I_{CM}	500		
Base current	I_B	100		
Peak base current	I_{BM}	200		
Total power dissipation, $T_s = 74\text{ °C}$	P_{tot}	360		mW
Junction temperature	T_j	150		°C
Storage temperature range	T_{stg}	− 65 ... + 150		

Thermal Resistance

Junction - ambient ²⁾	$R_{th\ JA}$	≤ 280	K/W
Junction - soldering point	$R_{th\ JS}$	≤ 210	

¹⁾ For detailed information see chapter Package Outlines.

²⁾ Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristicsat $T_A = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Collector-emitter breakdown voltage $I_C = 1\text{ mA}$	$V_{(BR)CE0}$	250 300	— —	— —	V
Collector-base breakdown voltage $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CB0}$	250 300	— —	— —	
Emitter-base breakdown voltage $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EB0}$	5	—	—	
Collector-base cutoff current $V_{CB} = 200\text{ V}$	I_{CB0}	—	—	100	nA
$V_{CB} = 250\text{ V}$		—	—	100	nA
$V_{CB} = 200\text{ V}, T_A = 150\text{ °C}$		—	—	20	μA
$V_{CB} = 250\text{ V}, T_A = 150\text{ °C}$		—	—	20	μA
Emitter-base cutoff current $V_{EB} = 3\text{ V}$	I_{EB0}	—	—	100	nA
DC current gain $I_C = 1\text{ mA}, V_{CE} = 10\text{ V}$	h_{FE}	25	—	—	—
$I_C = 10\text{ mA}, V_{CE} = 10\text{ V}^{1)}$		40	—	—	
$I_C = 30\text{ mA}, V_{CE} = 10\text{ V}^{1)}$		40	—	—	
		30	—	—	
Collector-emitter saturation voltage ¹⁾ $I_C = 20\text{ mA}, I_B = 2\text{ mA}$	V_{CEsat}	— —	— —	0.4 0.5	V
Base-emitter saturation voltage ¹⁾ $I_C = 20\text{ mA}, I_B = 2\text{ mA}$	V_{BEsat}	—	—	0.9	

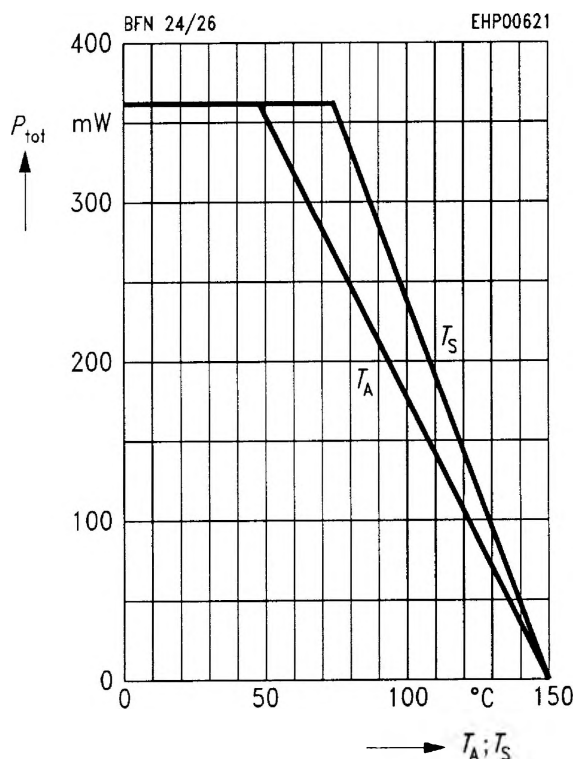
AC characteristics

Transition frequency $I_C = 20\text{ mA}, V_{CE} = 10\text{ V}, f = 20\text{ MHz}$	f_T	—	70	—	MHz
Output capacitance $V_{CB} = 30\text{ V}, f = 1\text{ MHz}$	C_{obo}	—	1.5	—	pF

¹⁾ Pulse test conditions: $t \leq 300\text{ }\mu\text{s}$, $D = 2\text{ %}$.

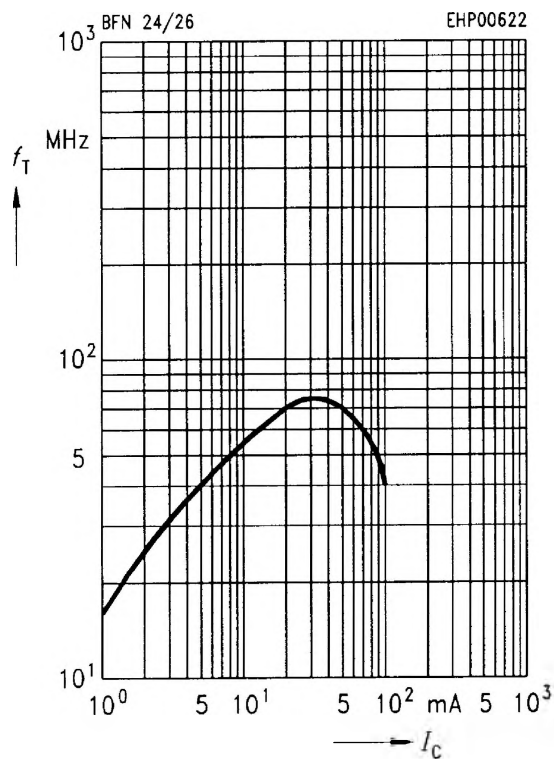
Total power dissipation $P_{\text{tot}} = f(T_A^*; T_S)$

* Package mounted on epoxy



Transition frequency $f_T = f(I_C)$

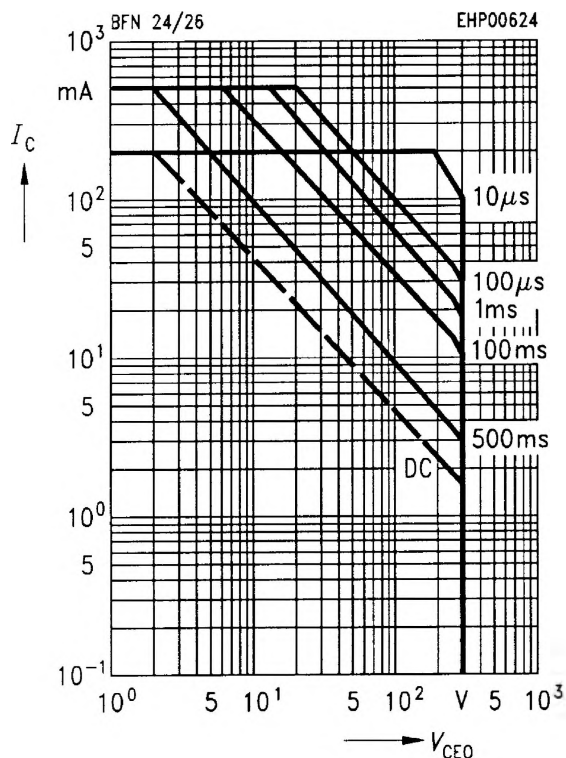
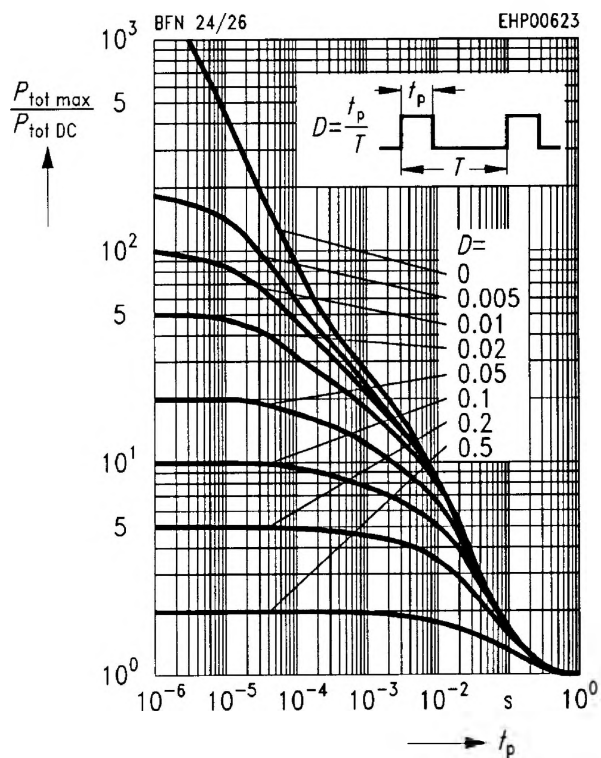
$V_{CE} = 10 \text{ V}$



Permissible pulse load $P_{\text{tot max}} / P_{\text{tot DC}} = f(t_p)$

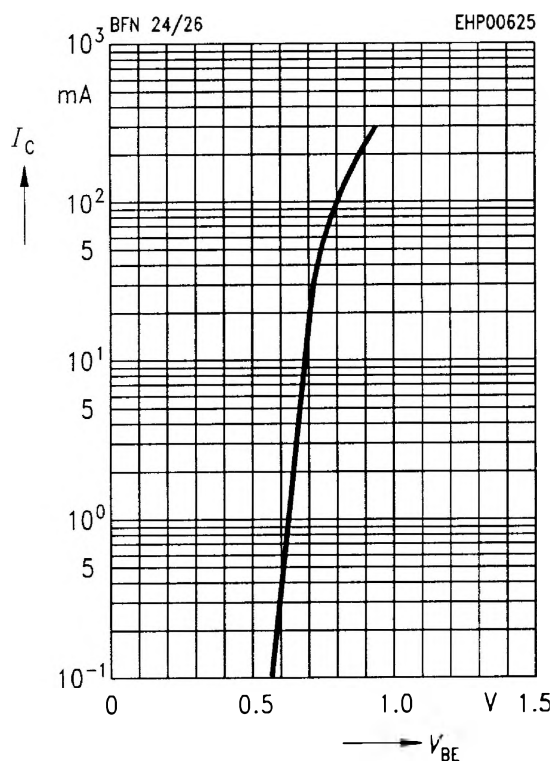
Operating range $I_C = f(V_{CE0})$

$T_A = 25 \text{ °C}, D = 0$



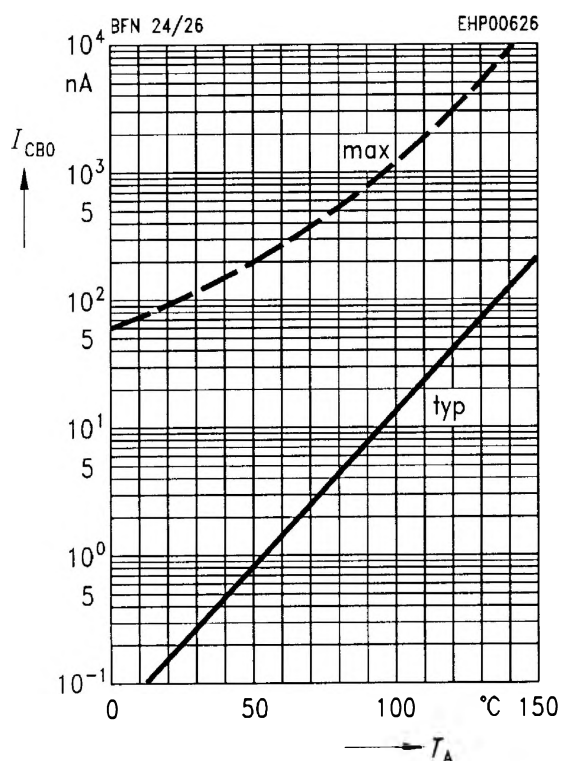
Collector current $I_C = f(V_{BE})$

$V_{CE} = 10 \text{ V}$



Collector cutoff current $I_{CB0} = f(T_A)$

$V_{CB} = 200 \text{ V}$



DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 10 \text{ V}$

